UTG6N65-S

**Preliminary** 

Insulated Gate Bipolar Transistor

# **650V TRENCH GATE** FIELD-STOP IGBT

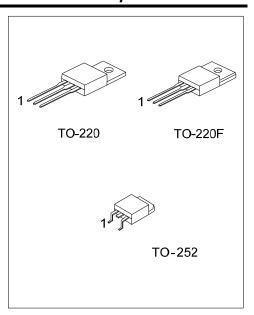
#### DESCRIPTION

The UTC UTG6N65-S is an Trench Field-Stop Insulated Gate Bipolar Transistor, it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

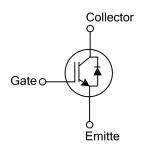
The UTC UTG6N65-S is suitable for the resonant or soft switching applications.

#### **FEATURES**

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage: V<sub>CE(SAT),Typ.</sub>=1.47V @ I<sub>C</sub>=6.0A, V<sub>GE</sub>=15V  $(T_C = 25^{\circ}C)$



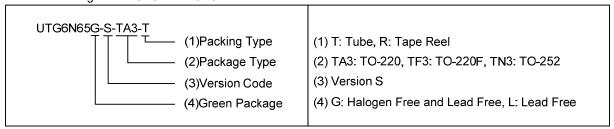
#### **SYMBOL**



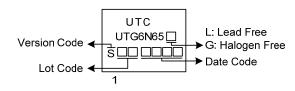
#### ORDERING INFORMATION

Ordering Number		Daakana	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG6N65L-S-TA3-T	UTG6N65G-S-TA3-T	TO-220	G	С	Е	Tube	
UTG6N65L-S-TF3-T	UTG6N65G-S-TF3-T	TO-220F	G	С	Е	Tube	
UTG6N65L-S-TN3-R	UTG6N65G-S-TN3-R	TO-252	G	С	Е	Tape Reel	

C: Collector Note: Pin Assignment: G: Gate E: Emitter



### **MARKING**



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#### ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	650	V
Gate-Emitter Voltage		.,	±20	V
Transient Gate-emitter voltage (tp < 5 ms)		$V_{GES}$	±25	V
Continuous Collector Current	T <sub>C</sub> =25°C	] ,	12	Α
	T <sub>C</sub> =100°C	Ic	6	Α
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	24	Α
Diode Forward Current	T <sub>C</sub> =25°C		12	Α
	T <sub>C</sub> =100°C	l <sub>F</sub>	6	Α
Short Circuit Withstand Time $V_{GE} = 15V$ , $V_{CC} \le 200V$ Allowed number of short circuits < 1000 Time between short circuits: $\ge 1.0s$ $T_{V,I} = 25^{\circ}C$		tsc	3	μs
Power Dissipation (T <sub>C</sub> =25°C)	TO-220		93	W
	TO-220F	P <sub>D</sub>	30	W
	TO-252		39	W
Operating Junction Temperature		TJ	-40 ~ +150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

## **■ THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Case	TO-220		1.34	°C/W
	TO-220F	θις	4.167	°C/W
	TO-252		3.205 (Note)	°C/W

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

<sup>2.</sup> Pulse width limited by maximum junction temperature.

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off Characteristics						
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>		650			V
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =650V, V <sub>GE</sub> =0V			5	μΑ
G-E Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V			±100	nA
On Characteristics	_					
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>	4.0		6.5	V
Collector to Emitter Saturation Voltage	Vce(sat)	I <sub>C</sub> =6.0A, V <sub>GE</sub> =15V T <sub>C</sub> =25°C T <sub>C</sub> =125°C		1.47 1.9	2.1	V
Dynamic Characteristics		10-123 3		1.0	1	
Input Capacitance	CIES			598		pF
Output Capacitance	Coes	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz		37.8		pF
Reverse Transfer Capacitance	Cres	7		10.7		pF
Switching Characteristics						
Total Gate Charge	Q <sub>G</sub>			49.4		nC
Gate-Emitter Charge	Q <sub>GE</sub>	V <sub>CE</sub> =520V, I <sub>C</sub> =6.0A, V <sub>GE</sub> =15V		14.3		nC
Gate-Collector Charge	Q <sub>GC</sub>			21.9		nC
Turn-On Delay Time	t <sub>DON)</sub>			15		ns
Rise Time	t <sub>R</sub>			19		ns
Turn-Off Delay Time	t <sub>DOFF)</sub>	$V_{CC}$ =400V, $I_{C}$ =6.0A, $R_{G}$ =5 $\Omega$ ,		39		ns
Fall Time	t <sub>F</sub>	V <sub>GE</sub> =0~15V, L=1000µH		290		ns
Turn-On Switching Loss	Eon			0.154		mJ
Turn-Off Switching Loss	Eoff			0.147		mJ
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTE	RISTICS	_			
Forward Voltage Drop	VF	I <sub>F</sub> =6.0A		1.6	3.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =6.0A, dI/dt=100A/μS,		43.8		ns
Reverse Recovery Charge	Qrr	Vcc=400V		3.8		nC

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